## Amendment to the claims:

Claims 1-44 (Canceled).

- 45. (Previously added): An apparatus for delivering media to a wafer, comprising: a housing defining a process chamber;
- a media delivery member coupled to the process chamber;
- a spin chuck positioned in the process chamber, the spin chuck having a wafer support surface, wherein the wafer support surface is <u>formed with silicon oxide coated contact points</u> [covered with a coating layer, the coating layer being in a solid state and substantially free of voids]; and

a vacuum supply line coupled to the spin chuck.

- 46. (Previously added): The apparatus of claim 45, wherein the coating layer is a dielectric coating layer.
- 47. (Previously added): The apparatus of claim 45, wherein the coating layer has a composition including a substance from the chemical family SiO<sub>x</sub>CH<sub>y</sub>, with x ranging from 1-2, inclusive, and y ranging from 0-3, inclusive.
  - 48. (Canceled)
- 49. (Currently amended): The apparatus of claim 45, wherein the coating layer material has a mechanical hardness equal to hardness<sub>coating layer</sub> and the wafer material has a mechanical hardness equal to hardness<sub>wafer</sub>, and wherein hardness coating layer is less than hardness<sub>wafer</sub>. [a corresponding mechanical hardness of the wafer.]
- 50. (Currently amended): The apparatus of claim 45, wherein the coating layer material has a mechanical hardness equal to hardness<sub>coating layer</sub>, and silicon has a mechanical hardness equal to hardness<sub>silicon</sub>, and wherein hardness<sub>coating layer</sub> is less than hardness<sub>silicon</sub>.[a mechanical hardness of silicon.]
- 51. (Previously added): The apparatus of claim 45, wherein the coating layer has a thickness in the range of 10-100 micrometers.
- 52. (Previously added): The apparatus of claim 45, wherein the coating layer has a thickness in the range of 1-10 micrometers.
- 53. (Previously added): The apparatus of claim 45, wherein the coating layer has a thickness in the range of 0.05-1 micrometers.

131

- 54. (Previously added): The apparatus of claim 45, wherein the coating material on the wafer support surface has a thickness of 10-100 microns.
- 55. (Previously added): The apparatus of claim 45, wherein the wafer support surface has a surface area no larger than a surface area of a wafer configured to be positioned on the wafer support surface.
- 56. (Previously added): The apparatus of claim 45, wherein the wafer support surface includes a plurality of support structures.
  - 57. (Canceled).
- 58. (Previously added): The apparatus of claim 45, wherein the wafer support surface includes a vacuum ring.
- 59. (Previously added): The apparatus of claim 59, wherein the vacuum ring is a line contact vacuum ring.
- 60. (Previously added): An apparatus of claim 45, further comprising a skirt positioned at a periphery and in a non-planar relationship to the wafer support wafer surface.
- 61. (Previously added): The apparatus of claim 60, wherein the wafer support surface provides a mechanical support for a wafer and the skirt is positioned to be in a non-mechanical supporting position relative to the wafer.
- 62. (Previously added): The apparatus of claim 60, wherein the skirt is sized to permit a wafer positioned on the wafer support surface to extend beyond a periphery of the skirt.
- 63. (Previously added): The apparatus of claim 60, wherein the skirt and wafer support surface are sized to be at least equal to a size of a wafer positioned on the wafer support surface.
- 64. (Previously added): The apparatus of claim 45, further comprising at least one wafer transporter coupled to the process chamber.

